



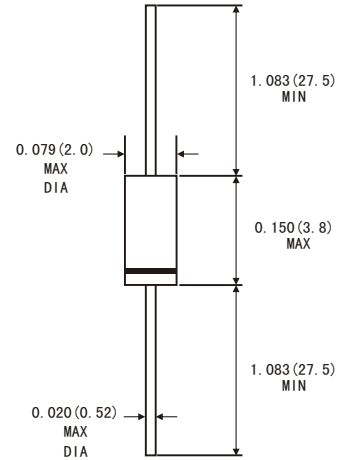
FEATURES

- Metal-on-silicon junction
- Low turn-on voltage
- Ultrafast switching speed
- Primarily intended for high level UHF mixers and ultrafast switching applications
- The diode is also available in the MiniMELF case with type designation LL45.
- High temperature soldering guaranteed: 260°C/10 seconds at terminals

MECHANICAL DATA

- Case: DO-35 glass case
- Polarity: color band denotes cathode end
- Weight: Approx. 0.13 gram

DO-35



Dimensions in inches and (millimeters)

ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	Units
Peak Reverse Voltage	V_{RRM}	15	V
Forward Continuous Current	I_F	30	mA
Surge non repetitive forward current $t_p \leq 1s$	I_{FSM}	60	mA
Junction and Storage temperature range	T_{STG} T_J	-65 to+150 -65 to+125	°C
Maximum Lead Temperature for Soldering during 10s at 4mm from Case	T_L	230	°C

ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	Unis
Reverse breakover voltage at $I_R=10\mu A$	V_R	15			V
Leakage current at $V_R=6V$	I_R			100	nA
Forward voltage drop at $I_F=1mA$ Test pulse: $t_p \leq 300\mu s$ $\delta < 2\%$ $I_F=10mA$ $I_F=30mA$	V_F			0.38 0.50 1	V
Junction Capacitance at $V_R=1V$, $f=1MHz$	C_J			1.1	pF
Thermal resistance	$R_{\theta JA}$			400	K/W



Figure 1. Forward current versus forward voltage at different temperatures (typical values)

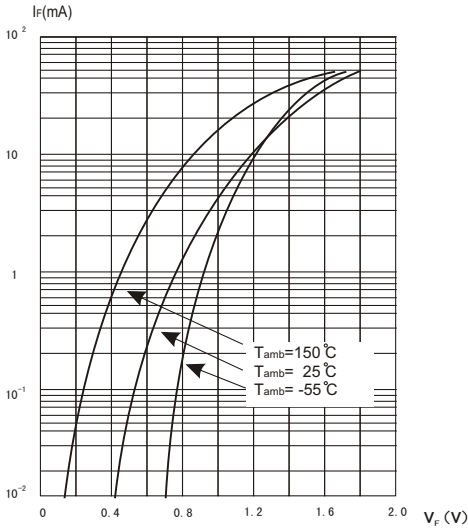


Figure 2. Capacitance C_J versus reverse applied voltage V_R (typical values)

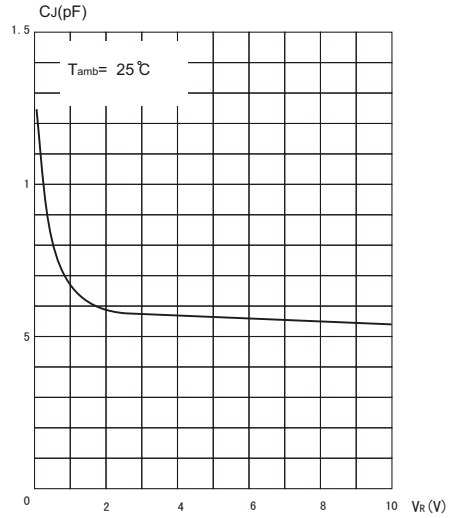


Figure 3. Reverse current versus ambient temperature

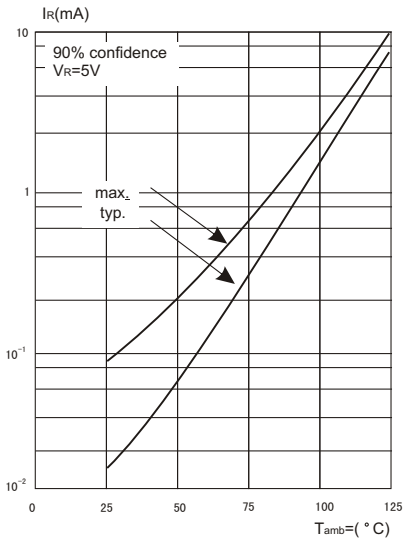


Figure 4. Reverse current versus continuous reverse voltage (typical values)

